

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC4336

DESCRIPTION

- With TO-220Fa package
- Fast switching speed
- Low collector saturation voltage

APPLICATIONS

- For use in switching power supplies ,DC/DC converters,motor drivers,solenoid drivers,etc

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

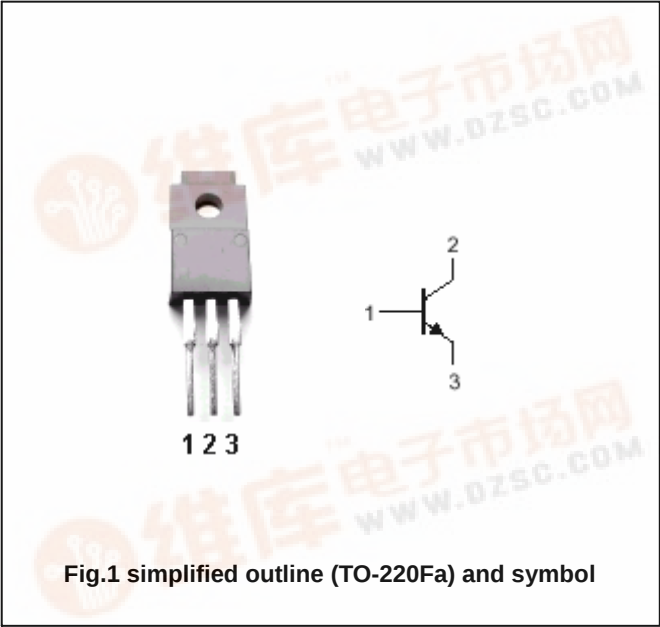


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		10	A
I _{CM}	Collector current-Peak		20	A
I _B	Base current(DC)		6	A
P _T	Total power dissipation	T _C =25	30	w
		T _a =25	2	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	



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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =5.0A, I _B =0.6A; L=1mH	100			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =6A; I _B =0.3A			0.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8A; I _B =0.4A			0.5	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =6A; I _B =0.3A			1.2	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =8A; I _B =0.4A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{CEX}	Collector cut-off current	V _{CE} =100V; V _{BE(off)} =-1.5V T _a =125			10 1.0	μA mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =1A; V _{CE} =2V	100			
h _{FE-2}	DC current gain	I _C =2A; V _{CE} =2V	100		400	
h _{FE-3}	DC current gain	I _C =6A; V _{CE} =2V	60			
C _{OB}	Collector capacitance	I _E =0; V _{CB} =10V; f=1MHz		120		pF
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V		150		MHz

Switching times

t _{on}	Turn-on time	I _C =6A; I _{B1} =I _{B2} =0.3A V _{CC} ≈ 50V; R _L =8.3Ω			0.3	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.3	μs

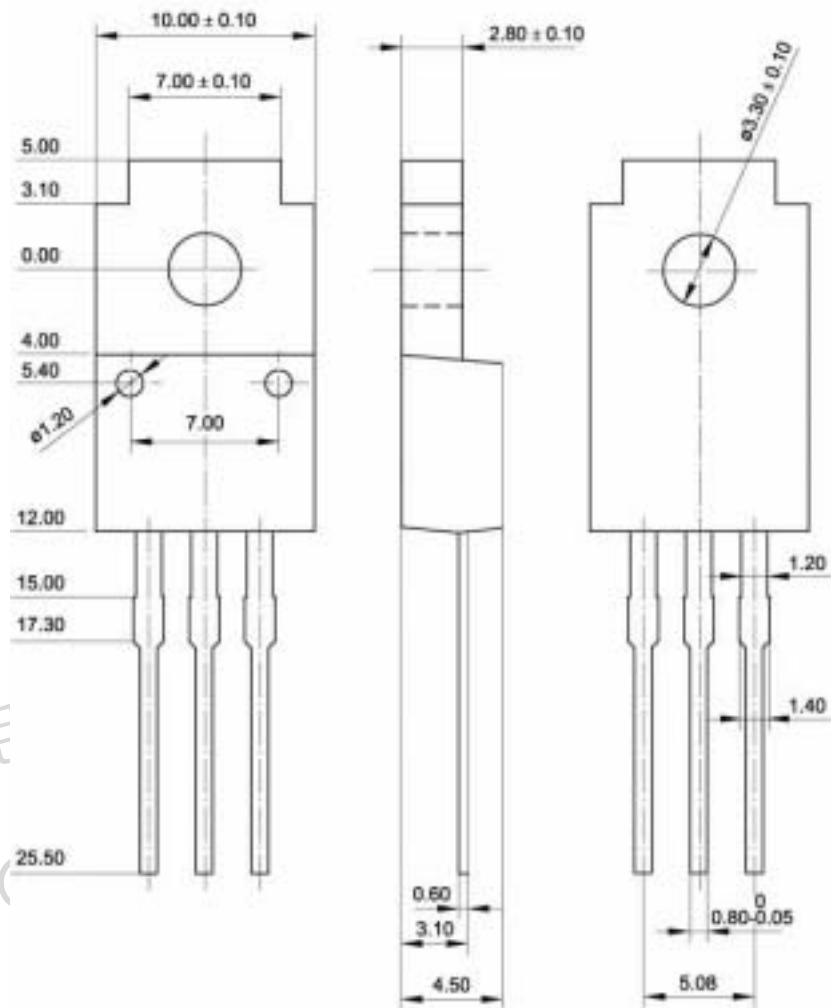
◆ h_{FE-2} Classifications

M	L	N
100-200	150-300	200-400

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)